

AMENDMENTS TO THE SPECIFICATION

Please amend the title as follows:

METHOD FOR SEMICONDUCTOR DEVICE MANUFACTURING ~~SEMI-~~
~~CONDUCTOR DEVICE~~ TO INCLUDE MULTISTAGE CHEMICAL VAPOR DEPOSITION
OF MATERIAL OXIDE FILM

Please amend specification paragraph [0008] as follows:

[0008] When forming the tantalum oxide film by the CVD method conventionally, as described above, ~~conventionally~~ an oxidizing gas such as an oxygen gas is used together with a material gas containing tantalum in order to fill oxygen vacancies liable to occur in the tantalum oxide film when it is being formed and also to remove organic residue. If oxygen vacancies are generated in the tantalum oxide film, ~~such a drawback occurs in that~~ a leakage current may flow through the formed capacitor, resulting in formation of the capacitive insulating film having a poor film quality.

[0045] FIGS. 1A-1C ~~are flow diagrams for showing a~~ show configurations of a semiconductor device manufacturing method, along steps thereof, according to a first embodiment of the present invention;

[0046] FIGS. 1D-1E ~~are continued flow diagrams for showing~~ continue to show the configurations of the semiconductor device manufacturing method along the steps thereof according to the first embodiment of the present invention;